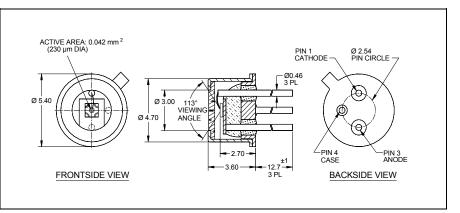


Pacific Silicon Sensor Series 9 Data Sheet Part Description AD230-9-TO52-S1 Order # 06-013





FEATURES

- + \varnothing 230 µm active area
- Low slope multiplication curve
- High speed, low noise
- NIR enhanced

DESCRIPTION

0.042 mm² High Speed, Low Noise Avalanche Photodiode with N on P construction. Hermetically packaged in a TO-52-S1 with a clear borosilicate glass window cap.

APPLICATIONS

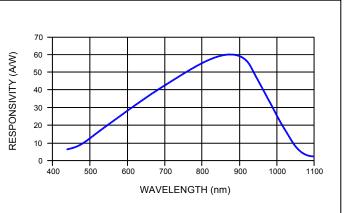
- High speed optical communications
- Laser range finder
- Medical equipment
- High speed photometry



ABSOLUTE MAXIMUM RATING

SYMBOL	PARAMETER	MIN	MAX	UNITS	
T _{STG}	Storage Temp	-55	+125 °C		
T _{OP}	Operating Temp	-40	+100	°C	
TSOLDERING	Soldering Temp 10 seconds		+260	°C	
	Electrical Power Dissipation @ 22°C	-	100	mW	
	Optical Peak Value, once for 1 second	-	200	mW	
I _{PH} (DC)	Continuous Optical Operation	-	250	μA	
I _{PH} (AC)	Pulsed Signal Input 50 µs "on" / 1 ms "off"	-	1	mA	

SPECTRAL RESPONSE at M = 100

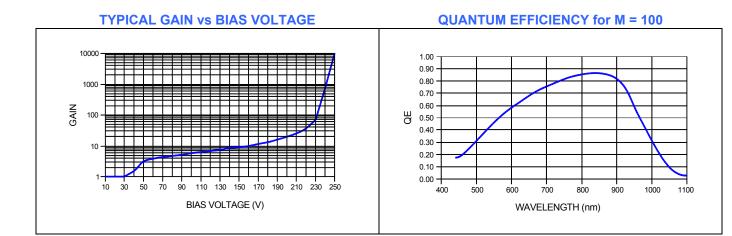


ELECTRO-OPTICAL CHARACTERISTICS @ 22 °C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Ι _D	Dark Current	M = 100*		0.5	1.5	nA
С	Capacitance	M = 100*		0.8		pF
V _{BR}	Breakdown Voltage	I _D = 2 μA	160	240		V
	Temperature Coefficient of V _{BR}			1.55		V/K
	Responsivity	M = 100; = 0 V; λ = 905 nm	55	60		A/W
$\Delta f_{ m 3dB}$	Bandwidth	-3dB		0.6		GHz
tr	Rise Time	M = 100		500		ps
	Optimum Gain		50	60		
	"Excess Noise" factor	M = 100		2.5		
	"Excess Noise" index	M = 100		0.2		
	Noise Current	M = 100		0.5		pA/Hz ^{1/2}
	Max Gain		200			
NEP	Noise Equivalent Power	M = 100; λ = 905 nm		1.0 X 10 ⁻¹⁴		W/Hz ^{1/2}

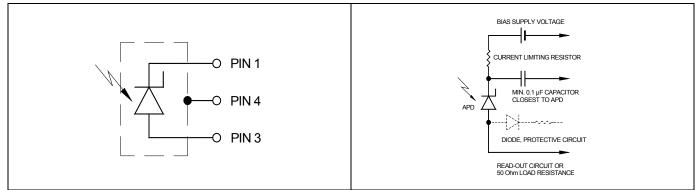
* Measurement conditions: Setup of photo current 1 nA at M = 1 and irradiated by a 880 nm, 80 nm bandwidth LED. Increase the photo current up to 100 nA, (M = 100) by internal multiplication due to an increasing bias voltage.

Disclaimer: Due to our policy of continued development, specifications are subject to change without notice.



DEVICE SCHEMATIC

SUGGESTED CIRCUIT SCHEMATIC



APPLICATION NOTES

- Current should be limited by a protecting resistor or current limiting IC inside the power supply.
- Use of low noise read-out IC.
- For high gain applications (M>50) bias voltage should be temperature compensated.
- For low light level applications, blocking of ambient light should be used.

HANDLING PRECAUTIONS:

- Soldering temperature 260°C for 10 seconds max. The device must be protected against solder flux vapor.
- Minimum pin length 2 mm
- · ESD protection Standard precautionary measures are sufficient.
- Storage Store devices in conductive foam.
- Avoid skin contact with window.
- · Clean window with Ethyl alcohol if necessary.
- Do not scratch or abrade window.

USA:

Pacific Silicon Sensor, Inc. 5700 Corsa Avenue, #105 Westlake Village, CA 91362 USA Phone (818) 706-3400 Fax (818) 889-7053 Email: <u>sales@pacific-sensor.com</u> www.pacific-sensor.com

International sales:

Silicon Sensor International AG Peter-Behrens-Str. 15 D-12459 Berlin, Germany Phone +49 (0)30-63 99 23 10 Fax +49 (0)30-63 99 23 33 Email: <u>sales@silicon-sensor.de</u> www.silicon-sensor.de

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